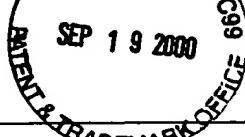


INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

SEP 19 2000



Docket Number	Application Number
M4065.0210/P210	09/588,008
Applicant(s)	
Dan Gealy et al.	
Filing Date	Group Art Unit
June 6, 2000	2814

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translations
							YES

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

A	G. W. Dietz et al., "LEAKAGE CURRENTS IN $Ba_{0.7}Sr_{0.3}TiO_3$ THIN FILMS FOR ULTRAHIGH-DENSITY DYNAMIC RANDOM ACCESS MEMORIES," J. Appl. Phys. 82 (5), September 1, 1997, American Institute of Physics, pages 2359-2364.
B	Tomonori Aoyama et al., "ULTRATHIN $Ta_2O_5$ FILM CAPACITOR WITH Ru BOTTOM ELECTRODE," J. Electrochem. Soc. Vol. 145, No. 8, August 1998, The Electrochemical Society, Inc., pages 2961-2963.
C	Benjamin Chih-ming Lai et al., "LEAKAGE CURRENT MECHANISM OF METAL- $Ta_2O_5$ METAL CAPACITORS FOR MEMORY DEVICE APPLICATION," Journal of the Electrical Society, 146 (1) pages 266-269 (1999).

EXAMINER	DATE CONSIDERED
Not Yet Assigned	<i>Vicki Trinh</i> 12/30/01
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.	

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